



ABSTRACT



POWER-SAVING READING OF MAGNETIC MEMORY DEVICES

The present disclosure relates to power-saving reading of magnetic memory devices. In one arrangement, a method comprises pulsing a voltage on the array, and obtaining a voltage value indicative of a memory state of the target memory cell from the voltage pulse using a sensing circuit that is electrically connected to the target memory cell. In another arrangement, a method comprises pulsing an array voltage on a plurality of row and column conductors of the array, connecting a sensing circuit to a conductor that is electrically coupled to the target memory cell, the sensing circuit including a sense element, and determining the voltage drop across the sense element of the sensing circuit during the voltage pulse, the voltage drop being indicative of a memory stage of the target memory cell.

(FIG. 11)